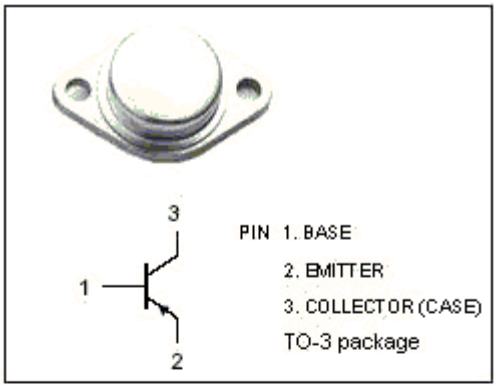
isc Silicon PNP Power Transistors 2SB653

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -100V(Min)
- High Power Dissipation-
  : P_C= 60W(Max)@T_C=25℃
- Complement to Type 2SD673

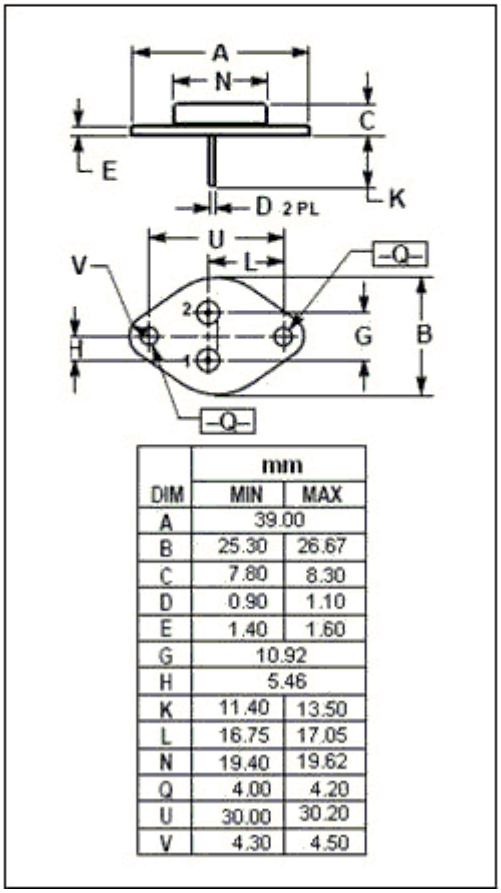


APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-12	A
I_B	Base Current-Continuous	-2	A
P_C	Collector Power Dissipation @T_C=25℃	60	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm	
	MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA; R_{BE}= ∞	-100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -5mA; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -1A; V_{CE}= -5V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0			-1	mA
h_{FE-1}	DC Current Gain	I_C= -1A; V_{CE}= -5V	60		200	
h_{FE-2}	DC Current Gain	I_C= -5A; V_{CE}= -5V	20			
f_T	Current-Gain—Bandwidth Product	I_C= -1A; V_{CE}= -5V		22		MHz
t_f	Fall Time	I_C= -0.6A; I_{B1}= -0.6A; I_{B2}= 0		0.5		μs

◆ **h_{FE} Classifications**

B	C
60-120	100-200